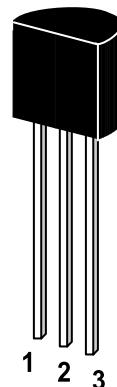


PNP Silicon Epitaxial Planar Transistor

for high voltage switching and amplifier applications.

The transistor is subdivided into one group according to its DC current gain. As complementary type the NPN transistor MPSA 44 is recommended.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector

TO-92 Plastic Package

Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	400	V
Collector Emitter Voltage	$-V_{CEO}$	400	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	300	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-I_C=1\text{mA}$, $-V_{CE}=10\text{V}$	h_{FE}	25	-	-	-
at $-I_C=10\text{mA}$, $-V_{CE}=10\text{V}$	h_{FE}	40	-	-	-
at $-I_C=30\text{mA}$, $-V_{CE}=10\text{V}$	h_{FE}	25	-	-	-
Emitter Cutoff Current at $-V_{EB}=4\text{V}$	$-I_{EBO}$	-	-	0.1	μA
Collector Cutoff Current at $-V_{CB}=300\text{V}$	$-I_{CBO}$	-	-	0.1	μA
Collector Cutoff Current at $-V_{CE}=400\text{V}$	$-I_{CES}$	-	-	1	μA
Collector Base Breakdown Voltage at $-I_C=100\mu\text{A}$	$-V_{(BR)CBO}$	400	-	-	V
Collector Emitter Breakdown Voltage at $-I_C=1\text{mA}$	$-V_{(BR)CEO}$	400	-	-	V
Emitter Base Breakdown Voltage at $-I_E=10\mu\text{A}$	$-V_{(BR)EBO}$	6	-	-	V
Collector Emitter Breakdown Voltage at $-I_C=100\mu\text{A}$	$-V_{(BR)CES}$	400	-	-	V
Collector Saturation Voltage at $-I_C=10\text{mA}$, $-I_B=1\text{mA}$	$-V_{CE(sat)}$	-	-	0.5	V
at $-I_C=50\text{mA}$, $-I_B=5\text{mA}$	$-V_{CE(sat)}$	-	-	0.75	V
Base Saturation Voltage at $-I_C=10\text{mA}$, $-I_B=1\text{mA}$	$-V_{BE(sat)}$	-	-	0.75	V
Collector Output Capacitance at $-V_{CB}=20\text{V}$, $f=1\text{MHz}$	C_{ob}	-	-	7	pF